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- as to the identity of the inventor (Rule 4.17(i))
- as to applicant's entitlement to apply for and be granted a patent (Rule 4.17(ii))
- as to the applicant's entitlement to claim the priority of the earlier application (Rule 4.17(iii))

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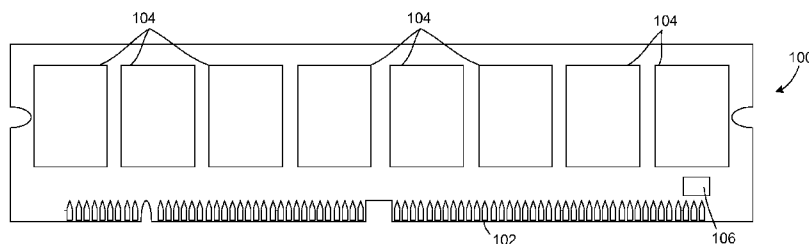


FIG. 1

(57) Abstract: A memory apparatus (100) enables operation which is adapted to environmental conditions. The memory apparatus (100) includes a memory module (102) that can store and incorporate environment-dependent optimal operating parameters. The memory module (102) comprises a plurality of volatile memory devices (104) and one or more non-volatile memory devices (106) that store a plurality of environment-dependent device parameters for a device selected from the plurality of volatile memory devices (104). The stored parameters enable the selected device to function optimally in multiple environmental conditions.



## MEMORY MODULE INCLUDING ENVIRONMENTAL OPTIMIZATION

### BACKGROUND

**[0001]** A dual in-line memory module (DIMM) comprises a series of dynamic random access memory integrated circuits. The modules are mounted on a printed circuit board and designed for use in personal computers, workstations, servers, and other systems. For various technologies, various bus and device clock frequencies are standardized.

**[0002]** A DIMM's capacity and timing parameters may be identified with Serial Presence Detect (SPD), generally an additional integrated circuit chip which contains information about the module type.

**[0003]** Conventional DIMM SPD registers only contain operating parameters that are specific to one voltage, frequency, and temperature. Joint Electron Device Engineering Council (JEDEC) standard 79-3A (DDR3 SDRAM Specification, September 2007) specifies operating parameters that are frequency dependent, but parameters for only one frequency (a "speed-bin") are supported in the SPD register. If desired to operate a DIMM at a

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slower speed than the DIMM's design speed, a conventional system enables hard-coding into system firmware of relevant operating parameters obtained from system tests at a voltages, frequencies, or temperatures that are different from conditions at which the memory, for example DRAM (dynamic random access memory), is tested. Such hard-coding of system firmware generally adds firmware complexity for selecting operating parameters that are optimal for multiple types of DIMMs, voltages, frequencies, and temperatures. Furthermore, hard-coding of system firmware can lead to unpredictable performance since different system designers can program different custom values for the parameters. Each system integrator may test the memory at a variety of different speeds and settings to determine the optimal settings for each configuration. Unfortunately, such testing involves a long process for each integrator and any information attained is not available to all users of the DIMM. Additionally, the information is not stored with the part but instead in a separate location on each system that would have to be updated regularly as new parts become available. No standardization exists for determining timings for parts running at a frequency different than the vendor-specified frequency.

## SUMMARY

**[0004]** Embodiments of a memory apparatus enable operation adapted to environmental conditions. The memory apparatus includes a memory module that can store and incorporate environment-dependent optimal operating parameters. The memory module comprises a plurality of volatile memory devices and one or more non-volatile memory devices that store a plurality of environment-dependent device parameters for a device selected from the plurality of volatile memory devices. The stored parameters enable the selected device to function optimally in multiple environmental conditions.

## BRIEF DESCRIPTION OF THE DRAWINGS

**[0005]** Embodiments of the invention relating to both structure and method of operation may best be understood by referring to the following description and accompanying drawings:

**FIGURE 1** is a schematic pictorial diagram depicting an embodiment of a memory apparatus that enables operation adapted to environmental conditions;

**FIGURE 2** is a schematic block diagram showing an embodiment of a system that operates memory based on environmental conditions;

**FIGURES 3A** and **3B** are flow charts illustrating one or more embodiments or aspects of a method for manufacturing a memory apparatus that enables operation which is adapted to environmental conditions; and

**FIGURE 4** is an example table showing environment-dependent device parameters that can be stored in an embodiment of a memory apparatus or system.

## DETAILED DESCRIPTION

**[0006]** Embodiments of systems, memory systems, and methods for manufacturing such systems implement environment-dependent optimal operating parameters.

**[0007]** Environment-dependent optimal operating parameters for memory modules and systems can be programmed to simplify firmware complexity, lower overall system cost, reduce time-to-market, and increase compatibility of industry-standard parts. In a specific embodiment, environment-dependent

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operating parameters such as column address select (CAS) latencies (CL), write latencies (WL), and the like can be programmed for dual in-line memory modules (DIMMs) into a serial presence detect (SPD) register.

**[0008]** The embodiments of systems, memory modules, and associated operating techniques described herein implement environment-dependent optimal operating parameters to enable the automation of a system for optimizing the slower-speed performance of low-cost, high-volume DIMMs (dual in-line memory module) that are designed and specified to operate at a higher speed. Memory designed to operate at high bandwidth and relatively longer latencies (for example, 1333 mega transfers per second (MT/s) and 9-9-9 timing, signifying Column Address Strobe Latency (tCL) - RAS to CAS Delay (tRCD) - RAS precharge (tRP) timing) does not necessarily operate correctly with the same latency at a lower bandwidth (for example, 800 MT/s may be best with 7-7-7 timing). In some systems, a memory controller can be configured for a slower operating frequency than the low-cost, high-volume DIMMs that are supplied with the system. However, the DIMM only provides timing information on one bandwidth (the fastest operating speed of the DIMM) in the SPD, and the system has no a priori information to determine timings to use for slower operation. Some operating parameters are dependent on voltage, frequency, and temperature that can be optimized for performance, cooling, and power.

**[0009]** The illustrative configuration that supports environment-dependent optimal operating parameters enables industry standard DIMMs to be used in a wider range of systems than the environment (voltage, frequency, temperature) at which the DIMMs were tested. Functional testing and DIMM qualifications are simplified, which decreases the time-to-market for a given system.

**[0010]** Referring to **FIGURE 1**, a schematic pictorial diagram illustrates an embodiment of a memory apparatus **100** that enables operation which is adapted to environmental conditions. The memory apparatus **100** includes a

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memory module **102** that can store and incorporate environment-dependent optimal operating parameters. The memory module **102** comprises a plurality of volatile memory devices **104** and one or more non-volatile memory devices **106** that store a plurality of environment-dependent device parameters for a device selected from the plurality of volatile memory devices **104**. The stored parameters enable the selected device to function optimally in multiple environmental conditions.

**[0011]** The one or more non-volatile memory devices **104** store the plurality of environment-dependent device parameters for at least one of the plurality of volatile memory devices **104**. The device parameters uniquely correspond to multiple environmental conditions for individual devices of the plurality of volatile memory devices **104**.

**[0012]** In an example implementation, the parameters can be assigned to an individual volatile memory device for a range of supply voltages, operating frequencies, and temperatures. Examples of environment-dependent device parameters include column address select (CAS) latencies supported, CAS write latency, minimum row precharge time, minimum row active to row active delay, active to active interval, reference command period, minimum row address select (RAS)-to-CAS delay, minimum active to precharge time, internal read command to first data interval, and the like. A particular implementation of the memory apparatus **100** can support any number of selected parameters.

**[0013]** In an example application, the environment-dependent device parameters can be selected to enable optimization of slower-speed performance of dual in-line memory modules (DIMMs) that are specified to operate at a speed which is higher than the slower-speed.

**[0014]** In various applications, the environment-dependent device parameters can be selected for optimization of performance, cooling, and

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power for multiple applied voltages, operating frequencies, and operating temperature.

**[0015]** The volatile memory devices **104** and non-volatile memory devices **106** can be any suitable memory components and devices. In a specific example, the non-volatile memory device **106** can be an electrically-erasable programmable read-only memory (EEPROM) that supports serial presence detect (SPD) with SPD memory space allocated to include the environment-dependent device parameters. The memory module **102** can be a dual in-line memory module (DIMM) with multiple mounted dynamic random access memory (DRAM) integrated circuits.

**[0016]** Referring to **FIGURE 2**, a schematic block diagram illustrates an embodiment of a system **200** that operates memory based on environmental conditions. The illustrative system **200** comprises a processor **210** and a memory module **202** coupled to the processor **210**. The illustrative memory module **202** comprises a plurality of memory devices **204** and parameters database **212** which stores multiple environment-dependent device parameters for individual devices of the plurality of memory devices **204**. The parameters enable the individual device to function optimally in multiple environmental conditions.

**[0017]** The memory devices **204** can be any suitable type of device. For example, the memory devices **204** can be dynamic random access memory (DRAM) devices.

**[0018]** The parameters database **212** stores the multiple environment-dependent device parameters for at least one of the plurality of memory devices **204**. The device parameters uniquely corresponding to a multiple environmental conditions for a single device of the memory device plurality. The environment-dependent device parameters can be assigned to an individual memory device **204** for a range of supply voltages, operating frequencies, temperatures, and the like. In an example implementation,

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parameters can be selected from among column address select (CAS) latencies supported, CAS write latency, minimum row precharge time, minimum row active to row active delay, active to active interval, reference command period, minimum row address select (RAS)-to-CAS delay, minimum active to precharge time, internal read command to first data interval, and others.

**[0019]** The stored environment-dependent device parameters enable tailoring of operations to environmental conditions to enable optimization of aspects of operation including performance, cooling, and power for a plurality of applied voltages, operating frequencies, operating temperature, and the like. For example, the parameters can be selected to enable optimization of slower-speed performance of dual in-line memory modules (DIMMs) that are specified to operate at a speed higher than the slower-speed.

**[0020]** The system **200** can comprise a plurality of memory modules **202** coupled to the processor **210** with the memory modules **202** having at least some variability in environment-dependent device parameters. The processor **210** operates to compare the parameters database **212** programmed for the different memory modules **202** and determine optimal settings that enable the multiple memory modules **202** to operate at a maximum supported speed with parameters that all memory modules **202** are qualified to operate.

**[0021]** Various embodiments can incorporate any suitable components and devices. In a particular example implementation, the memory module **202** can be a dual in-line memory module (DIMM), the memory devices **204** can be dynamic random access memory (DRAM) integrated circuits mounted on the memory module **202**, and the parameters database **212** can be an electrically-erasable programmable read-only memory (EEPROM) that supports serial presence detect (SPD) wherein SPD memory space is allocated to include the plurality of environment-dependent device parameters.

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**[0022]** The system **200** can further comprise at least one sensor **214** that senses an environmental condition, and logic **216** coupled to the sensor and the memory module **202** that invokes a parameter set from the multiple environment-dependent device parameters based on the sensed environmental condition.

**[0023]** Referring to **FIGURES 3A** and **3B**, flow charts illustrate one or more embodiments or aspects of a method for manufacturing a memory apparatus that enables operation which is adapted to environmental conditions.

**FIGURE 3A** depicts a method for manufacturing **300** a memory apparatus that can store and incorporate environment-dependent optimal operating parameters. The illustrative method **300** comprises testing **302** a memory module at multiple environmental conditions and determining **304** a plurality of environment-dependent device parameters for operating memory devices in the memory module at the multiple environmental conditions. The plurality of environment-dependent device parameters are stored **306** in a parameters database. The environment-dependent device parameters enable the memory devices to function optimally in multiple environmental conditions.

**[0024]** **FIGURE 3B** shows an embodiment of a manufacturing method **310** that supports operation of the memory apparatus which is adapted for environmental conditions. The method **310** comprises testing **312** the memory module at a range of supply voltages, operating frequencies, and temperatures. The environment-dependent device parameters can be selected **314** from column address select (CAS) latencies supported, CAS write latency, minimum row precharge time, minimum row active to row active delay, active to active interval, reference command period, minimum row address select (RAS)-to-CAS delay, minimum active to precharge time, internal read command to first data interval, and others.

**[0025]** In some implementations, the environment-dependent device parameters can be selected **316** to enable optimization of slower-speed

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performance of dual in-line memory modules (DIMMs) that are specified to operate at a speed higher than the slower-speed.

**[0026]** Referring to **FIGURE 4**, an example table shows environment-dependent device parameters that can be stored an embodiment of a memory apparatus or system. An illustrative memory apparatus or system enables programming of multiple operating parameters into the SPD register of a given DIMM. Optimal operating parameters are supplied for a range of voltages, frequencies, and temperatures. Relevant operating parameters that may vary with the system environment may include but are not limited to CL: CAS latencies supported; CWL: CAS write latency; t<sub>RP</sub>: minimum row precharge time; t<sub>RRD</sub>: minimum row active to row active delay; t<sub>RC</sub>: active to active or REF command period; t<sub>RCD</sub>: minimum RAS-to-CAS delay; t<sub>RAS</sub>: minimum active to precharge time; t<sub>AA</sub>: internal read command to first data; and the like.

**[0027]** In the example, the space requirements in SPD EEPROM are allocated for four 4 speed grades times three voltages times two temperatures for a total of 24 settings in the SPD. Each setting is four 4-bit values, for a total of 48 bytes per table. In the example, the size of the table in non-volatile memory is given as 24 bytes for illustrative purposes only. In a particular implementation, any suitable size can be used since the range of possible values can be smaller or much larger.

**[0028]** In the example table, two rows for the highest speed operation are shown as blank. The concept is that a module can also contain information designating speeds at which the module is not designed to operate. Although shown as blank, the corresponding memory or logic for the blank elements is programmed or set to hold a value that indicates to the system either to prohibit running of the memory at that speed, or to expect failures and/or marginal behavior at the speed.

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**[0029]** The table depicted in **FIGURE 4** illustrates one embodiment of environment-dependent device parameters that can be stored in a system or memory device. Any suitable combination of parameters can be implemented in other configurations.

**[0030]** The systems, devices, and manufacturing techniques disclosed herein can eliminate the testing of systems to obtain operating parameters, thereby decreasing the time-to-market for a given system. System cost is reduced by enabling the use of high-volume parts in a system. Firmware complexity is also reduced because the SPD already contains operating parameters for a range of system environments. The correct operating parameters may be selected by reading the SPD register information from the DIMM. By testing the DIMMs at different frequencies, voltages, and temperatures, then supplying that information in the SPD, memory vendors can expect wider usage of parts that are designed to run at a higher frequency than system integrators desire. Support of environment-dependent device parameters enables the depicted systems and devices to store significantly less information about the memory used in the system by locating storage of the timing information directly on the DIMM. Improvements in memory process technology that allow higher speed operation can be exploited in a system that supports environment-dependent device parameters to enable memory to be transparently utilized by systems that read data from the SPD.

**[0031]** Terms “substantially”, “essentially”, or “approximately”, that may be used herein, relate to an industry-accepted tolerance to the corresponding term. Such an industry-accepted tolerance ranges from less than one percent to twenty percent and corresponds to, but is not limited to, functionality, values, process variations, sizes, operating speeds, and the like. The term “coupled”, as may be used herein, includes direct coupling and indirect coupling via another component, element, circuit, or module where, for indirect coupling, the intervening component, element, circuit, or module does not modify the information of a signal but may adjust its current level, voltage

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level, and/or power level. Inferred coupling, for example where one element is coupled to another element by inference, includes direct and indirect coupling between two elements in the same manner as “coupled”.

**[0032]** The illustrative block diagrams and flow charts depict process steps or blocks in a manufacturing process. Although the particular examples illustrate specific process steps or acts, many alternative implementations are possible and commonly made by simple design choice. Acts and steps may be executed in different order from the specific description herein, based on considerations of function, purpose, conformance to standard, legacy structure, and the like.

**[0033]** While the present disclosure describes various embodiments, these embodiments are to be understood as illustrative and do not limit the claim scope. Many variations, modifications, additions and improvements of the described embodiments are possible. For example, those having ordinary skill in the art will readily implement the steps necessary to provide the structures and methods disclosed herein, and will understand that the process parameters, materials, and dimensions are given by way of example only. The parameters, materials, and dimensions can be varied to achieve the desired structure as well as modifications, which are within the scope of the claims. Variations and modifications of the embodiments disclosed herein may also be made while remaining within the scope of the following claims.

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WHAT IS CLAIMED IS:

1. A memory apparatus comprising:  
a memory module comprising:  
a plurality of volatile memory devices; and  
at least one non-volatile memory device that stores a plurality of environment-dependent device parameters for an individual device of the plurality of volatile memory devices, the plurality of parameters enabling the individual device to function optimally in multiple environmental conditions.
2. The apparatus according to Claim 1 further comprising:  
the at least one non-volatile memory device storing the plurality of environment-dependent device parameters for at least one of the plurality of volatile memory devices, the device parameters uniquely corresponding to a plurality of environmental conditions for ones of the plurality of volatile memory devices.
3. The apparatus according to Claim 1 further comprising:  
the plurality of parameters assigned to an individual volatile memory device for a range of supply voltages, operating frequencies, and temperatures;  
the plurality of environment-dependent device parameters comprising at least one parameter selected from a group consisting of column address select (CAS) latencies supported, CAS write latency, minimum row precharge time, minimum row active to row active delay, active to active interval, reference command period, minimum row address select (RAS)-to-CAS delay, minimum active to precharge time, and internal read command to first data interval; and  
the plurality of environment-dependent device parameters selected for optimization of performance, cooling, and power for a plurality of

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applied voltages, operating frequencies, and operating temperature.

4. The apparatus according to Claim 1 further comprising:  
the plurality of environment-dependent device parameters selected to enable optimization of slower-speed performance of dual in-line memory modules (DIMMs) that are specified to operate at a speed higher than the slower-speed.
5. The apparatus according to Claim 1 further comprising:  
the at least one non-volatile memory device comprising an electrically-erasable programmable read-only memory (EEPROM) that supports serial presence detect (SPD) wherein SPD memory space is allocated to include the plurality of environment-dependent device parameters.
6. The apparatus according to Claim 1 further comprising:  
the memory module comprising a dual in-line memory module (DIMM) with a plurality of dynamic random access memory (DRAM) integrated circuits mounted thereon.
7. A system comprising:  
a processor; and  
a memory module coupled to the processor and comprising a plurality of memory devices and parameters database that stores a plurality of environment-dependent device parameters for an individual device of the plurality of memory devices, the plurality of parameters enabling the individual device to function optimally in multiple environmental conditions.
8. The system according to Claim 7 further comprising:  
the plurality of memory devices comprising dynamic random access memory devices.

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9. The system according to Claim 7 further comprising:  
the parameters database storing the plurality of environment-dependent device parameters for at least one of the plurality of memory devices, the device parameters uniquely corresponding to a plurality of environmental conditions for ones of the plurality of memory devices; and  
the plurality of environment-dependent device parameters assigned to an individual memory device for a range of supply voltages, operating frequencies, and temperatures.
10. The system according to Claim 7 further comprising:  
a plurality of memory modules coupled to the processor having at least some variability in environment-dependent device parameters, the processor operative to compare the parameters database programmed for different ones of the memory modules and determine optimal settings that enable the plurality of memory modules to operate at a maximum supported speed and with parameters that all memory modules are qualified to operate.
11. The system according to Claim 7 further comprising:  
the plurality of environment-dependent device parameters comprising at least one parameter selected from a group consisting of column address select (CAS) latencies supported, CAS write latency, minimum row precharge time, minimum row active to row active delay, active to active interval, reference command period, minimum row address select (RAS)-to-CAS delay, minimum active to precharge time, and internal read command to first data interval;  
the plurality of environment-dependent device parameters selected to enable optimization of slower-speed performance of dual in-line memory modules (DIMMs) that are specified to operate at a speed higher than the slower-speed; and

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the plurality of environment-dependent device parameters selected for optimization of performance, cooling, and power for a plurality of applied voltages, operating frequencies, and operating temperature.

12. The system according to Claim 7 further comprising:  
the parameters database comprising an electrically-erasable programmable read-only memory (EEPROM) that supports serial presence detect (SPD) wherein SPD memory space is allocated to include the plurality of environment-dependent device parameters;  
the memory module comprising a dual in-line memory module (DIMM);  
and  
the plurality of memory devices comprises a plurality of dynamic random access memory (DRAM) integrated circuits mounted on the memory module.

13. The system according to Claim 7 further comprising:  
at least one sensor that senses an environmental condition; and  
a logic coupled to the sensor and coupled to the memory module that invokes a parameter set from the plurality of environment-dependent device parameters based on the sensed environmental condition.

14. A method of manufacturing a memory apparatus comprising:  
testing a memory module at multiple environmental conditions;  
determining a plurality of environment-dependent device parameters for operating memory devices in the memory module at the multiple environmental conditions; and  
storing the plurality of environment-dependent device parameters in a parameters database, the plurality of environment-dependent device parameters enabling the memory devices to function optimally in multiple environmental conditions.

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15. The method according to Claim 14 further comprising:  
testing the memory module at a range of supply voltages, operating frequencies, and temperatures;  
selecting the plurality of environment-dependent device parameters from a group consisting of column address select (CAS) latencies supported, CAS write latency, minimum row precharge time, minimum row active to row active delay, active to active interval, reference command period, minimum row address select (RAS)-to-CAS delay, minimum active to precharge time, and internal read command to first data interval; and  
selecting the plurality of environment-dependent device parameters to enable optimization of slower-speed performance of dual in-line memory modules (DIMMs) that are specified to operate at a speed higher than the slower-speed.

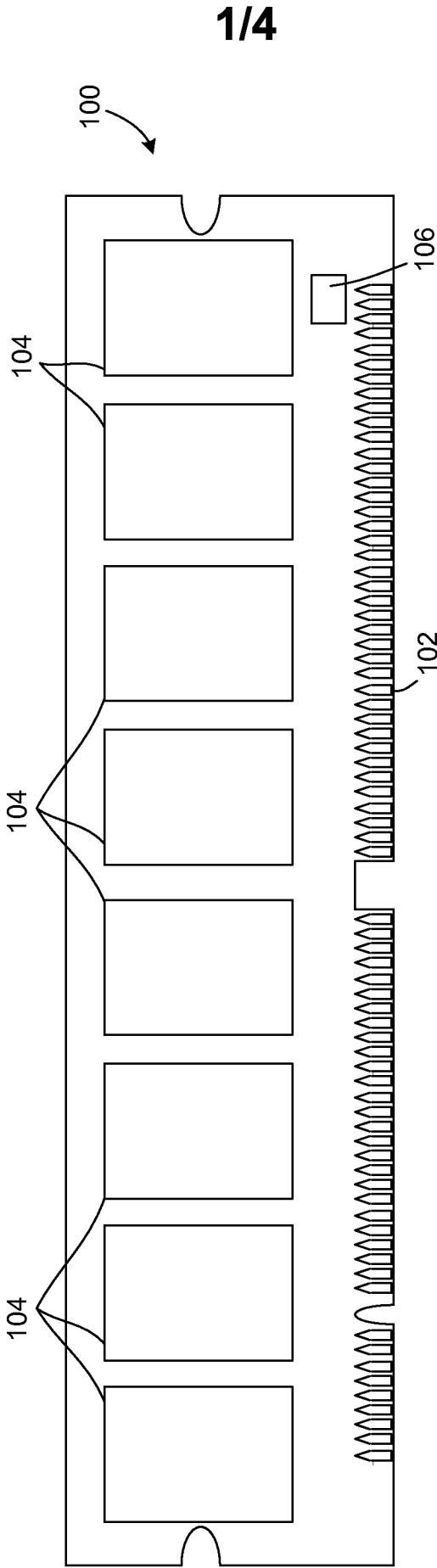


FIG. 1

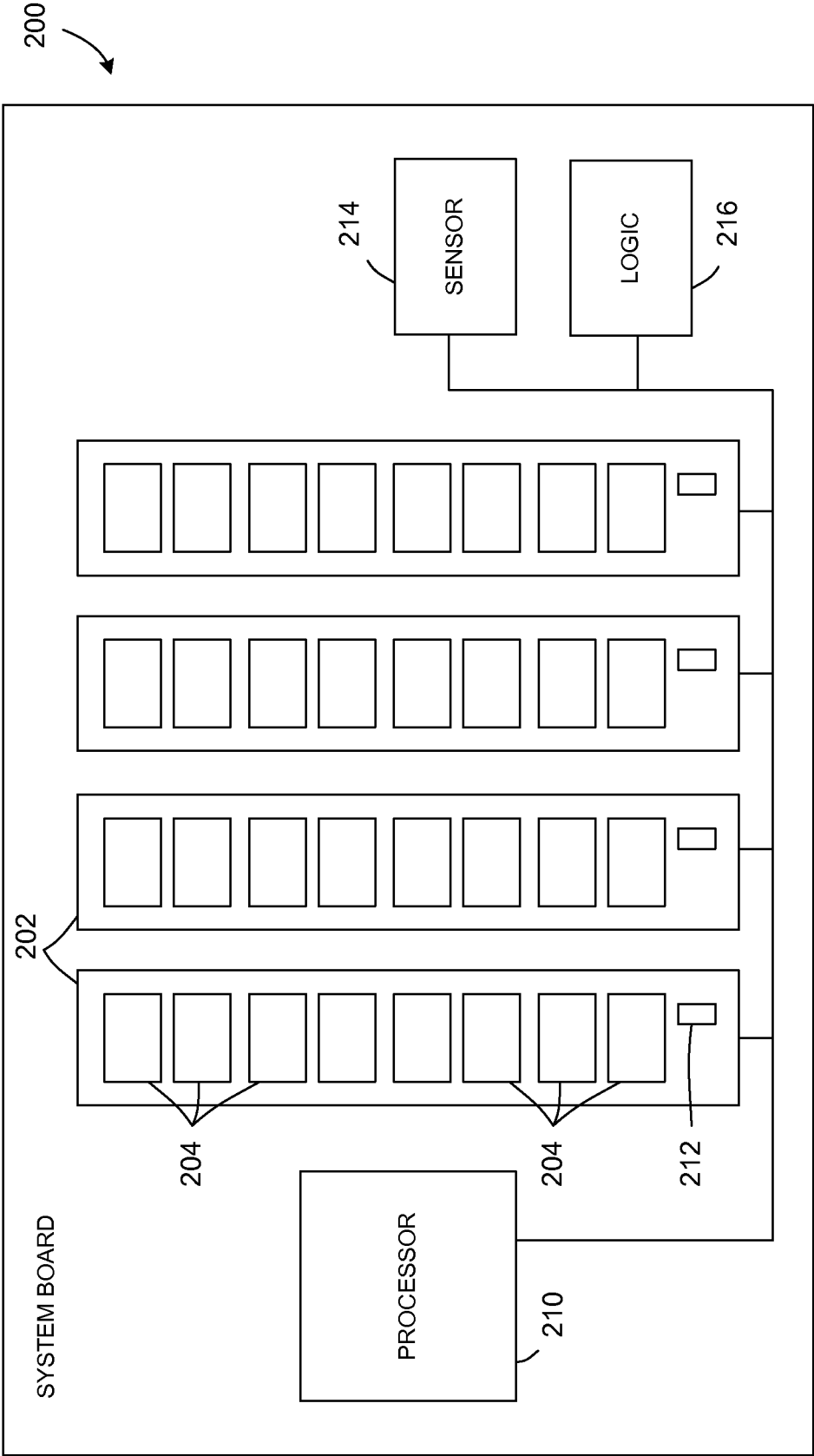


FIG. 2

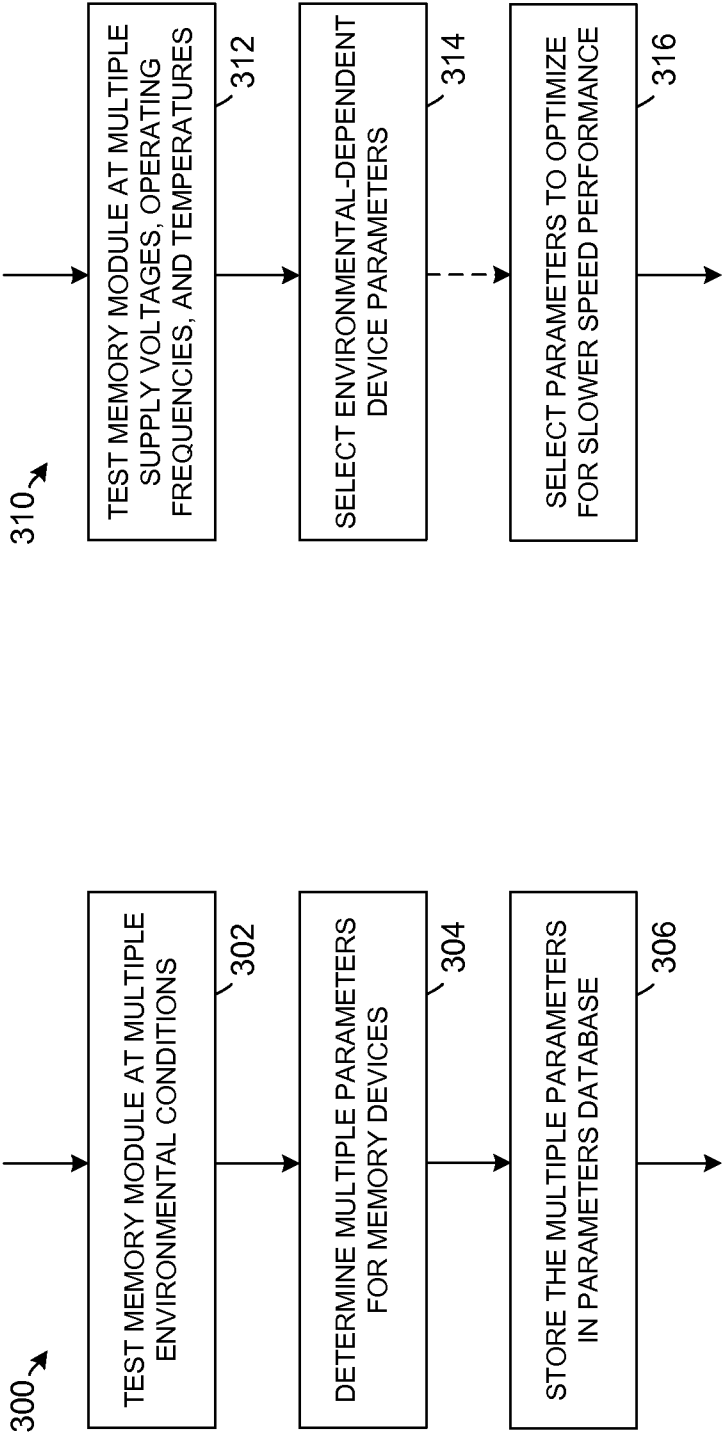


FIG. 3A

FIG. 3B

**4/4**

| <b>SPEED</b> | <b>VOLTAGE</b> | <b>TEMP</b> | <b>Trp</b> | <b>Trcd</b> | <b>Tras</b> | <b>Tcl</b> |
|--------------|----------------|-------------|------------|-------------|-------------|------------|
| 1333         | 1.65           | 55-80       | 9          | 9           | 9           | 4          |
|              | 1.65           | 0-55        | 8          | 8           | 8           | 3          |
|              | 1.5            | 55-80       | 9          | 9           | 9           | 3          |
|              | 1.5            | 0-55        | 8          | 8           | 8           | 3          |
|              | 1.35           | 55-80       | -          | -           | -           | -          |
|              | 1.35           | 0-55        | -          | -           | -           | -          |
| 1067         | 1.65           | 55-80       | 8          | 8           | 8           | 3          |
|              | 1.65           | 0-55        | 6          | 6           | 6           | 4          |
|              | 1.5            | 55-80       | 9          | 9           | 9           | 3          |
|              | 1.5            | 0-55        | 8          | 8           | 8           | 4          |
|              | 1.35           | 55-80       | 9          | 9           | 9           | 3          |
|              | 1.35           | 0-55        | 8          | 8           | 8           | 4          |
| 800          | 1.65           | 55-80       | 6          | 6           | 6           | 4          |
|              | 1.65           | 0-55        | 7          | 7           | 7           | 3          |
|              | 1.5            | 55-80       | 7          | 7           | 7           | 3          |
|              | 1.5            | 0-55        | 7          | 7           | 7           | 4          |
|              | 1.35           | 55-80       | 8          | 8           | 8           | 3          |
|              | 1.35           | 0-55        | 8          | 8           | 8           | 2.5        |

**FIG. 4**

## INTERNATIONAL SEARCH REPORT

International application No.  
**PCT/US2009/057875****A. CLASSIFICATION OF SUBJECT MATTER***G11C 11/4093(2006.01)i*

According to International Patent Classification (IPC) or to both national classification and IPC

**B. FIELDS SEARCHED**

Minimum documentation searched (classification system followed by classification symbols)

IPC: G11C; G06F

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Korean utility models and applications for utility models

Japanese utility models and applications for utility models

Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)

eKOMPASS(KIPO internal) &amp; Keywords: memory, environment, parameter

**C. DOCUMENTS CONSIDERED TO BE RELEVANT**

| Category* | Citation of document, with indication, where appropriate, of the relevant passages                             | Relevant to claim No. |
|-----------|----------------------------------------------------------------------------------------------------------------|-----------------------|
| X         | KR 10-2008-0095298 A (FUJITSU LIMITED) 28 October 2008<br>See figure 2-3 and paragraph [0042], [0073], [0076]. | 1-13                  |
| A         | US 2006-0083093 A1 (DOVER et al.) 20 April 2006<br>See abstract and figure 1.                                  | 1-15                  |
| A         | US 2008-0059690 A1 (MITTAL et al.) 06 March 2008<br>See abstract and figure 2.                                 | 1-15                  |

☐ Further documents are listed in the continuation of Box C.☒ See patent family annex.

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